

# PBSS4032PZ

# 30 V, 4.4 A PNP low V<sub>CEsat</sub> (BISS) transistor Rev. 01 — 31 March 2010

**Product data sheet** 

#### **Product profile** 1.

#### 1.1 General description

PNP low V<sub>CEsat</sub> Breakthrough In Small Signal (BISS) transistor in a medium power SOT223 (SC-73) Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS4032NZ.

#### 1.2 Features and benefits

- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- Optimized switching time
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain (h<sub>FE</sub>) at high I<sub>C</sub>
- High energy efficiency due to less heat generation
- AEC-Q101 qualified
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors

#### 1.3 Applications

- DC-to-DC conversion
- Battery-driven devices
- Power management
- Charging circuits

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	-30	V
I <sub>C</sub>	collector current		-	-	-4.4	Α
I <sub>CM</sub>	peak collector current	$\begin{array}{l} \text{single pulse;} \\ t_p \leq 1 \text{ ms} \end{array}$	-	-	-10	Α
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_{C} = -4 \text{ A};$ $I_{B} = -400 \text{ mA}$	<u>[1]</u> -	58	86	mΩ

<sup>[1]</sup> Pulse test:  $t_p \le 300~\mu s;~\delta \le 0.02.$ 



# 2. Pinning information

Table 2. Pinning

	9		
Pin	Description	Simplified outline	Graphic symbol
1	base		
2	collector	4	2, 4
3	emitter		1 —
4	collector		3
			sym028

# 3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PBSS4032PZ	SC-73	plastic surface-mounted package with increased heat sink; 4 leads	SOT223		

# 4. Marking

Table 4. Marking codes

3	
Type number	Marking code
PBSS4032PZ	PB4032PZ

# 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

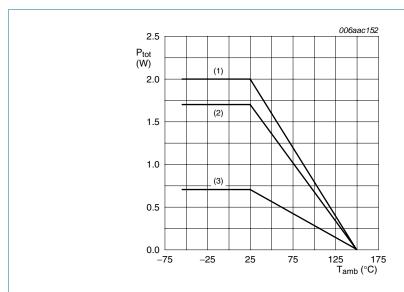
Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter	-	-30	V
$V_{CEO}$	collector-emitter voltage	open base	-	-30	V
$V_{EBO}$	emitter-base voltage	open collector	-	-5	V
I <sub>C</sub>	collector current		-	-4.4	Α
I <sub>CM</sub>	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	<b>–10</b>	Α
I <sub>B</sub>	base current		-	-1	Α

 Table 5.
 Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
P <sub>tot</sub>	total power dissipation	$T_{amb} \leq 25 ^{\circ}C$	<u> 11</u> -	700	mW
			[2] -	1700	mW
			[3] -	2000	mW
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-55	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [3] Device mounted on a ceramic PCB,  $Al_2O_3$ , standard footprint.



- (1) Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>
- (3) FR4 PCB, standard footprint

Fig 1. Power derating curves

## Thermal characteristics

Table 6. **Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
uily a)	thermal resistance from	in free air	<u>[1]</u> -	-	180	K/W
	junction to ambient		[2] _	-	75	K/W
			<u>[3]</u> _	-	65	K/W
$R_{th(j\text{-sp})}$	thermal resistance from junction to solder point		-	-	15	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.

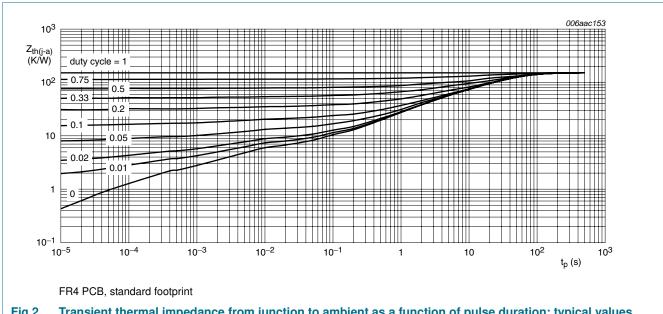


Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

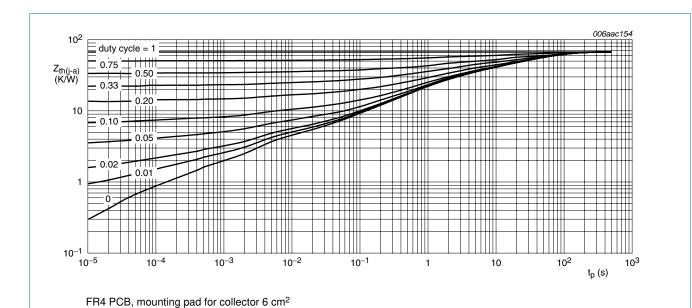
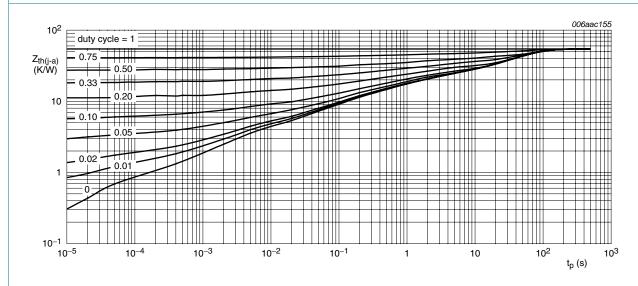


Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

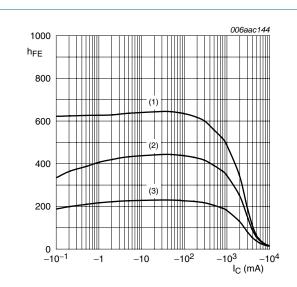
## 7. Characteristics

**Table 7. Characteristics** 

 $T_{amb}$  = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	$V_{CB} = -30 \text{ V}; I_E = 0 \text{ A}$		-	-	-100	nA
	current	$V_{CB} = -30 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150  ^{\circ}\text{C}$		-	-	-55	μΑ
I <sub>CES</sub>	collector-emitter cut-off current	$V_{CE} = -24 \text{ V}; V_{BE} = 0 \text{ V}$		-	-	-100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$		-	-	-100	nA
h <sub>FE</sub>	DC current gain		[1]				
		$V_{CE} = -2 \text{ V};$ $I_{C} = -500 \text{ mA}$		200	350	-	
		$V_{CE} = -2 \text{ V}; I_{C} = -1 \text{ A}$		200	320	-	
		$V_{CE} = -2 \text{ V}; I_{C} = -2 \text{ A}$		150	240	-	
		$V_{CE} = -2 \text{ V}; I_{C} = -4 \text{ A}$		60	100	-	
V <sub>CEsat</sub>	collector-emitter		[1]				
	saturation voltage	$I_C = -1 \text{ A}; I_B = -50 \text{ mA}$		-	-110	-165	mV
		$I_C = -1 \text{ A}; I_B = -10 \text{ mA}$		-	-160	-240	mV
	$I_C = -2 \text{ A}; I_B = -40 \text{ mA}$		-	-200	-300	mV	
	$I_C = -4 \text{ A}; I_B = -400 \text{ mA}$		-	-230	-345	mV	
		$I_C = -4 \text{ A}; I_B = -200 \text{ mA}$		-	-270	-400	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C = -4 A$ ; $I_B = -400 \text{ mA}$	[1]	-	58	86	mΩ
V <sub>BEsat</sub>	base-emitter	$I_C = -1 A$ ; $I_B = -100 \text{ mA}$	[1]	-	-0.79	-0.9	V
	saturation voltage	$I_C = -4 \text{ A}; I_B = -400 \text{ mA}$	[1]	-	-0.99	-1.05	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE} = -2 \text{ V}; I_{C} = -2 \text{ A}$	<u>[1]</u>	-	-0.81	-0.9	V
t <sub>d</sub>	delay time	$V_{CC} = -12.5 \text{ V};$		-	30	-	ns
t <sub>r</sub>	rise time	$I_C = -1 \text{ A}; I_{Bon} = -0.05 \text{ A};$		-	60	-	ns
t <sub>on</sub>	turn-on time	$I_{Boff} = 0.05 \; A$		-	90	-	ns
t <sub>s</sub>	storage time			-	140	-	ns
t <sub>f</sub>	fall time			-	80	-	ns
t <sub>off</sub>	turn-off time			-	220	-	ns
f <sub>T</sub>	transition frequency	$V_{CE} = -10 \text{ V};$ $I_{C} = -100 \text{ mA};$ $f = 100 \text{ MHz}$		-	130	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB} = -10 \text{ V};$ $I_E = i_e = 0 \text{ A}; f = 1 \text{ MHz}$		-	65	-	pF

<sup>[1]</sup> Pulse test:  $t_p \leq 300~\mu s;~\delta \leq 0.02.$ 



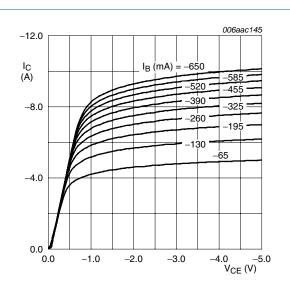
$$V_{CE} = -2 V$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

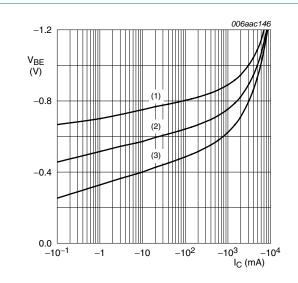
(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig 5. DC current gain as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$ 

Fig 6. Collector current as a function of collector-emitter voltage; typical values



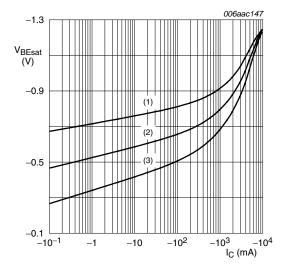
$$V_{CE} = -2 \text{ V}$$

(1) 
$$T_{amb} = -55 \,^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 7. Base-emitter voltage as a function of collector current; typical values



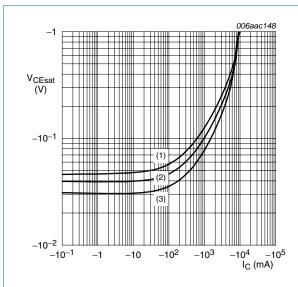
 $I_{\rm C}/I_{\rm B} = 20$ 

(1) 
$$T_{amb} = -55 \,^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig 8. Base-emitter saturation voltage as a function of collector current; typical values



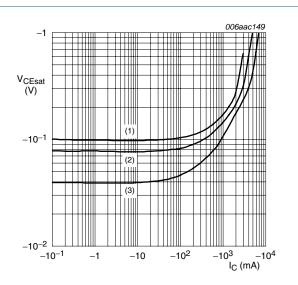
$$I_C/I_B = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig 9. Collector-emitter saturation voltage as a function of collector current; typical values



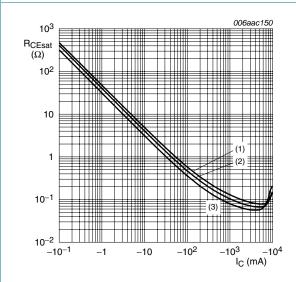
$$T_{amb} = 25 \, ^{\circ}C$$

(1) 
$$I_C/I_B = 100$$

(2) 
$$I_C/I_B = 50$$

(3) 
$$I_C/I_B = 10$$

Fig 10. Collector-emitter saturation voltage as a function of collector current; typical values



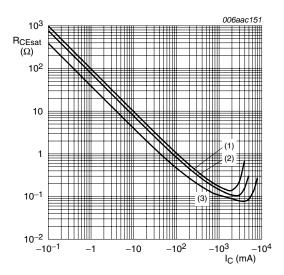
$$I_{C}/I_{B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 11. Collector-emitter saturation resistance as a function of collector current; typical values



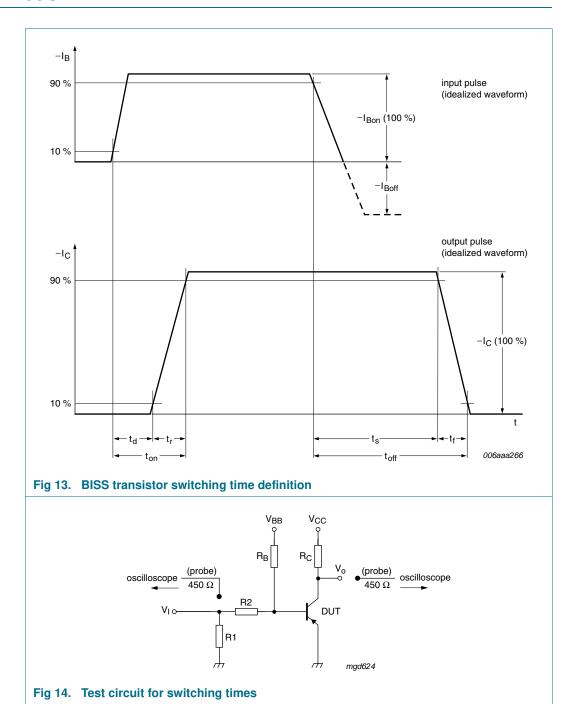
(1) 
$$I_C/I_B = 100$$

(2) 
$$I_C/I_B = 50$$

(3)  $I_C/I_B = 10$ 

Fig 12. Collector-emitter saturation resistance as a function of collector current; typical values

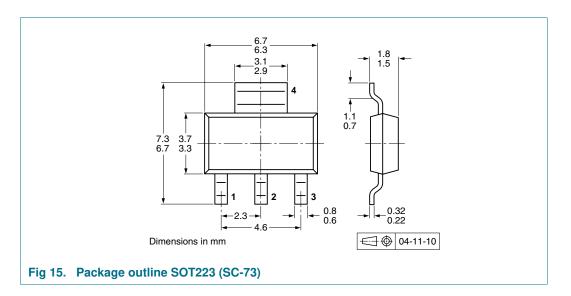
## 8. Test information



## 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

# 9. Package outline



# 10. Packing information

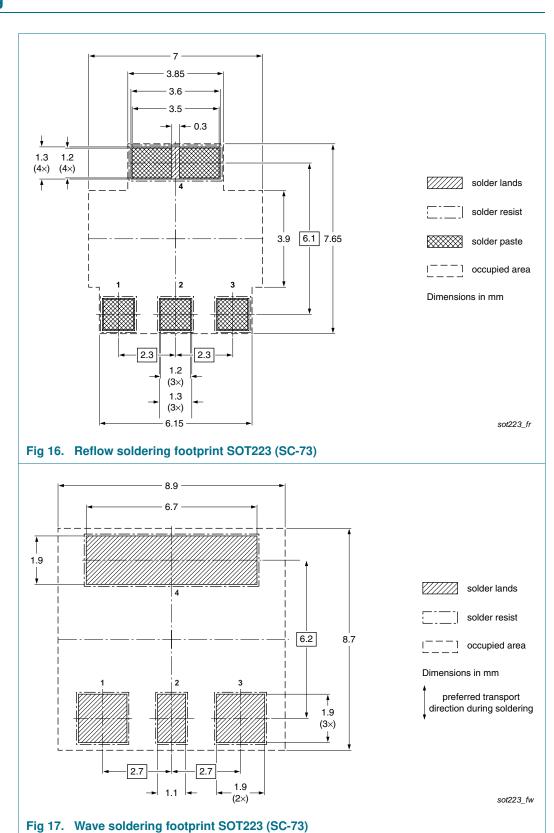
Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing q	cking quantity	
			1000	4000	
PBSS4032PZ	SOT223	8 mm pitch, 12 mm tape and reel	-115	-135	

<sup>[1]</sup> For further information and the availability of packing methods, see Section 14.

# 11. Soldering



Nexperia PBSS4032PZ

30 V, 4.4 A PNP low V<sub>CEsat</sub> (BISS) transistor

# 12. Revision history

## Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4032PZ_1	20100331	Product data sheet	-	-

## 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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30 V, 4.4 A PNP low V<sub>CEsat</sub> (BISS) transistor

## 14. Contact information

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For sales office addresses, please send an email to:  $\underline{\textbf{salesaddresses@nexperia}}.\textbf{com}$ 

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